

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 7,075,150 B2  
APPLICATION NO. : 10/725849  
DATED : July 11, 2006  
INVENTOR(S) : Diane C. Boyd et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 12, Line 45.:

"50.0mn" should read -- 50.0 nm --

Column 12, Line 54.:

"The semiconducting" should read -- The semiconducting --

Column 12, Line 58.:

"comprise a doped region of sai SOI layer"

should read

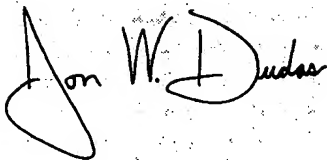
-- comprise a doped region of said SOI layer --

Column 13, Line 5.:

"uried sinsulating" should read -- buried insulating --

Signed and Sealed this

Fourteenth Day of November, 2006

A handwritten signature in black ink, reading "Jon W. Dudas", is written over a rectangular area with a faint grid pattern.

JON W. DUDAS

*Director of the United States Patent and Trademark Office*